

OPA9411

Infrared LED Chip

GaAs /GaAs

1. Material Substrate GaAs (N Type)
 Epitaxial Layer GaAs (P/N Type)

2. Electrode N (Cathode) Side Gold Alloy
 P (Anode) Side Gold Alloy

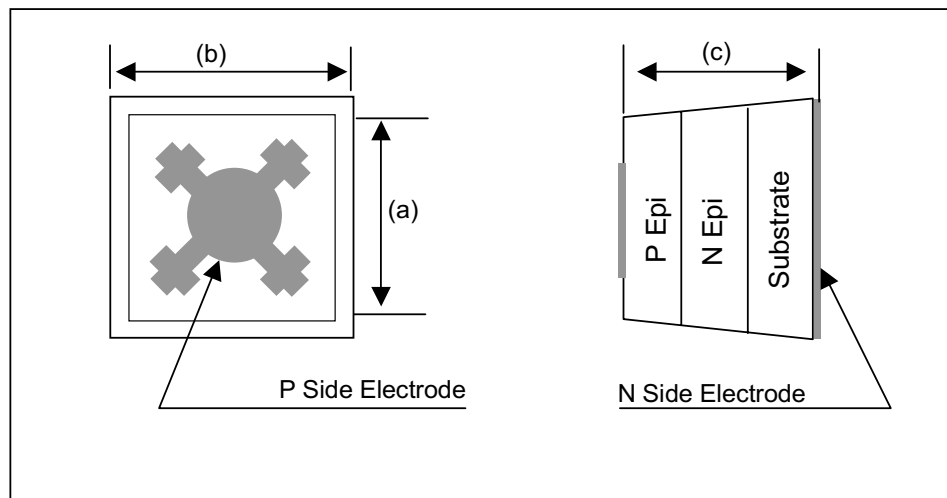
3. Electro-Optical Characteristics

Parameter	Symbol	Min	Typ	Max	Unit	Condition
Forward Voltage	$V_{F(1)}$		1.2		V	$I_F=20\text{mA}$
	$V_{F(2)}$		1.3	1.5	V	$I_F=100\text{mA}$
Reverse Voltage	V_R	5	30		V	$I_R=10\mu\text{A}$
Power	$P_{O(1)}$		4		mW	$I_F=20\text{mA}$
	$P_{O(2)}$	8	13		mW	$I_F=100\text{mA}$
Wavelength	λ_P		940		nm	$I_F=20\text{mA}$
	$\Delta\lambda$		45		nm	$I_F=20\text{mA}$

Note : Assembled into T1³/₄ plastic package.

4. Mechanical Data

- (a) Emission Area ----- 14mil × 14mil
- (b) Bottom Area ----- 16mil × 16mil
- (c) Chip Thickness ----- 11mil



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